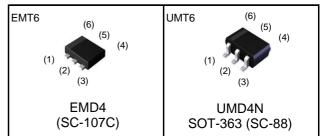
EMD4 / UMD4N

NPN + PNP Complex Digital Transistors (Bias Resistor Built-in Transistors)

<For DTr1(NPN)>

Parameter	Value
V _{CC}	50V
I _{C(MAX.)}	100mA
R ₁	47kΩ
R_2	47kΩ

Outline



Datasheet

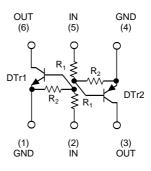
<For DTr2(PNP)>

Parameter	Value
V _{CC}	-50V
I _{C(MAX.)}	-100mA
R ₁	10kΩ
R_2	47kΩ

Features

- 1) Both the DTC144E chip and DTA114Y chip in one package.
- 2) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making the circuit design easy.
- 5) Lead Free/RoHS Compliant.

•Inner circuit



Application

Inverter circuit, Interface circuit, Driver circuit

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMD4	EMT6	1616	T2R	180	8	8,000	D4
UMD4N	UMT6	2021	TR	180	8	3,000	D4

● Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	DTr1(NPN)	DTr2(PNP)	Unit
Supply voltage	V _{CC}	50	-50	V
Input voltage	V _{IN}	-10 to +40	-40 to +6	V
Output current	Io	30	-70	mA
Collector current	I _{C(MAX.)} *1	100	-100	mA
Power dissipation	P _D *2	150 (Total)*3		mW
Junction temperature	Tj	150		°C
Range of storage temperature	T _{stg}	–55 to	-55 to +150	

●Electrical characteristics(Ta = 25°C) <For DTr1(NPN)>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage	$V_{I(off)}$	$V_{CC} = 5V, I_{O} = 100 \mu A$	ı	1	0.5	V
input voitage	$V_{I(on)}$	$V_0 = 0.3V, I_0 = 2mA$	3.0	-	-	V
Output voltage	$V_{O(on)}$	$I_{O}/I_{I} = 10mA/0.5mA$	-	0.1	0.3	V
Input current	I _I	V _I = 5V	-	-	0.18	mA
Output current	I _{O(off)}	$V_{CC} = 50V, V_I = 0V$	ı	-	0.5	μΑ
DC current gain	Gı	$V_O = 5V$, $I_O = 5mA$	68	-	-	-
Input resistance	R ₁	-	32.9	47	61.1	kΩ
Resistance ratio	R ₂ /R ₁	-	0.8	1	1.2	-
Transition frequency	f _T *1	$V_{CE} = 10V, I_{E} = -5mA$ f = 100MHz		250		MHz

●Electrical characteristics(Ta = 25°C) <For DTr2(PNP)>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
In a set of the man	$V_{I(off)}$	$V_{CC} = -5V, I_{O} = -100 \mu A$	-	-	-0.3	V
Input voltage	V _{I(on)}	$V_0 = -0.3V, I_0 = -1mA$	-1.4	-	-	V
Output voltage	V _{O(on)}	$I_{O}/I_{I} = -5\text{mA}/-0.25\text{mA}$	-	-0.1	-0.3	V
Input current	I _I	$V_1 = -5V$	-	-	-0.88	mA
Output current	I _{O(off)}	$V_{CC} = -50V, V_I = 0V$	-	-	-0.5	μΑ
DC current gain	Gı	$V_0 = -5V, I_0 = -5mA$	68	-	-	-
Input resistance	R ₁	-	7	10	13	kΩ
Resistance ratio	R ₂ /R ₁	-	3.7	4.7	5.7	-
Transition frequency	f _T *1	$V_{CE} = -10V, I_{E} = 5mA$ f = 100MHz	-	250	-	MHz

^{*1} Characteristics of built-in transistor

^{*2} Each terminal mounted on a reference footprint

^{*3 120}mW per element must not be exceeded.

●Electrical characteristic curves (Ta = 25°C) <For DTr1(NPN)>

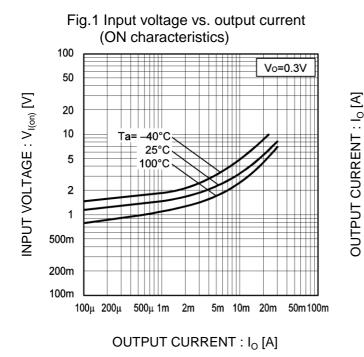


Fig.2 Output current vs. input voltage (OFF characteristics) 10m Vcc=5V 5m Ta=100°C 2m 25°C 1m 40°C 500μ 200μ 100μ 50μ 20μ 10μ 5μ 2μ 1μ 0 0.5 1.0 1.5 2.0 2.5 3.0 INPUT VOLTAGE : $V_{I(off)}[V]$

Fig.3 Output current vs. output voltage

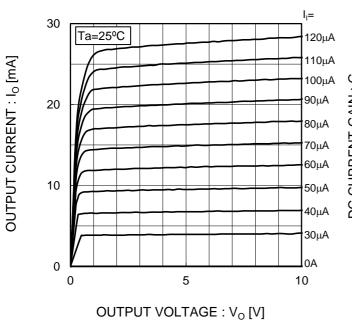
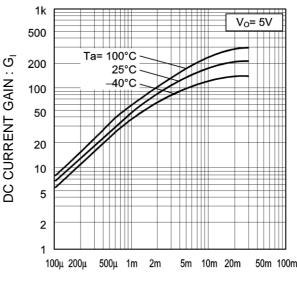


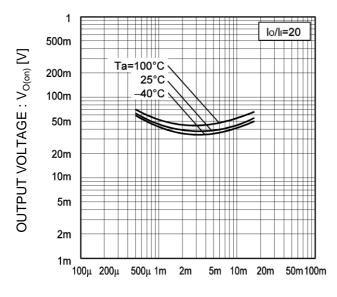
Fig.4 DC current gain vs. output current



OUTPUT CURRENT: Io [A]

●Electrical characteristic curves (Ta = 25°C) <For DTr1(NPN)>

Fig.5 Output voltage vs. output current



OUTPUT CURRENT : Io [A]

●Electrical characteristic curves (Ta = 25°C) <For DTr2(PNP)>

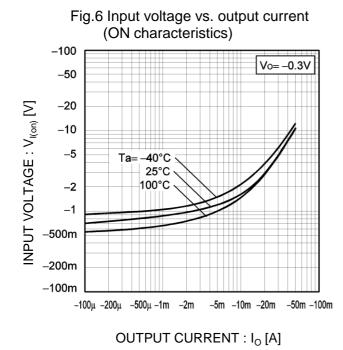


Fig.7 Output current vs. input voltage (OFF characteristics) -10m Vcc=-5V-5m –2m OUTPUT CURRENT: Io [A] -1m –500μ Ta=100°C –200μ 25°C –100μ 40°C -50μ -20μ –10μ **–**5μ -2μ -1μ -0.5 -1.0-1.5 -2.5 0 -2.0 -3.0INPUT VOLTAGE : $V_{I(off)}[V]$

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0

●Electrical characteristic curves (Ta = 25°C) <For DTr2(PNP)>

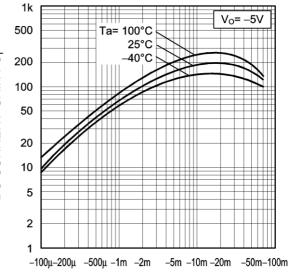
 $I_{I} = -500 \mu A - 450 \mu A$ –400μA -70 -350μΑ -60 OUTPUT CURRENT : Io [mA] -300μΑ -50 **JC CURRENT GAIN** -250μΑ -40 -200μΑ -30 150μΑ -20 100μΑ Ta=25ºC -10 -50μΑ 0

-5

OUTPUT VOLTAGE: Vo [V]

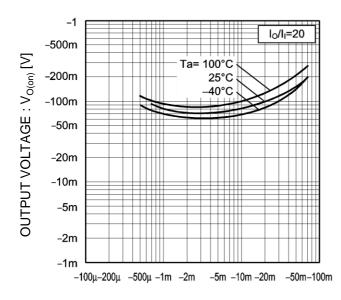
Fig.8 Output current vs. output voltage

Fig.9 DC current gain vs. output current



OUTPUT CURRENT: Io [A]

Fig.10 Output voltage vs. output current

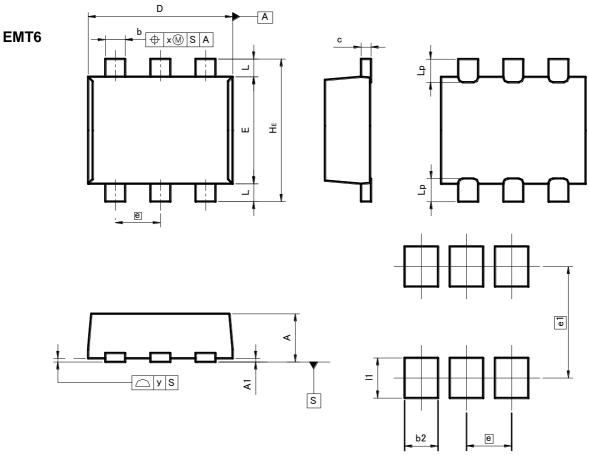


OUTPUT CURRENT : Io [A]

NΑ

-10

●Dimensions (Unit : mm)



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

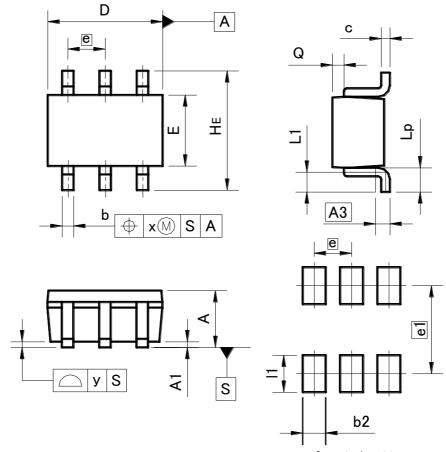
DIM	MILIM	ETERS	INCHES		
ואונט	MIN	MAX	MIN	MAX	
Α	0.45	0.55	0.018	0.022	
A1	0.00	0.10	0.000	0.004	
b	0.17	0.27	0.007	0.011	
С	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
Е	1.10	1.30	0.043	0.051	
е	0.50		0.020		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	_	0.35	-	0.014	
х	_	0.10		0.004	
у	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
DIM MIN		MAX	MIN	MAX	
b2	_	0.37	_	0.015	
e1	1.25		0.0	149	
l1	_	0.45	-	0.018	

Dimension in mm / inches

●Dimensions (Unit:mm)

UMT6



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM MILIME		ETERS	INC	HES
DIIVI	MIN	MAX	MIN	MAX
Α	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.3	25	0.0	10
b	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.0	.65 0.026		26
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
Х	_	0.10		0.004
У	_	0.10		0.004

DIM	MILIM	MILIMETERS		HES
MIN		MAX	MIN	MAX
b2	_	0.40	-	0.016
e1	1.55		0.0	61
l1	_	0.65	_	0.026

Dimension in mm / inches

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